

**Shanghai Sunmi Technology Co.,Ltd.**

Room 505, KIC Plaza, No.388 Song Hu Road, Yang Pu District, Shanghai, China  
Zhang Wentang 18721763396

---

**Request for Class II Permissive Change**

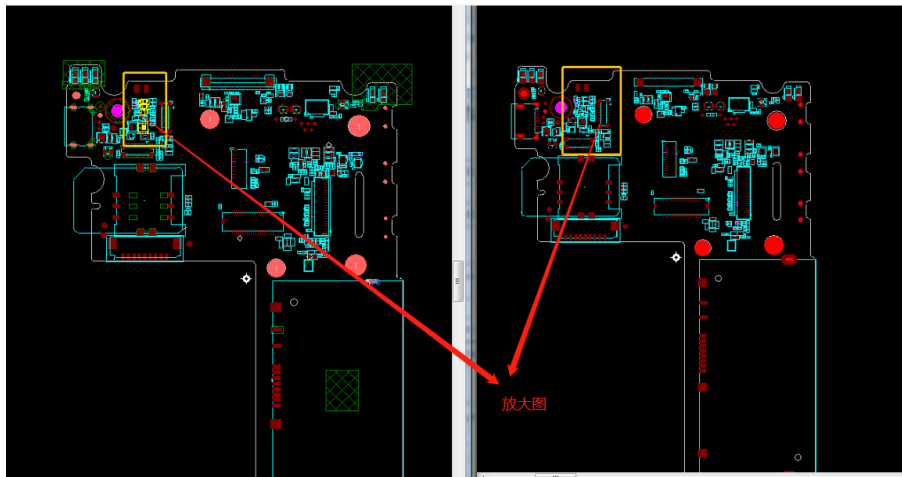
**FCC ID: 2AH25W6900**

**Date of Original Grant: 06/27/2018**

**TO: Federal Communication Commission**

Please be notified that we, the undersigned, **Shanghai Sunmi Technology Co.,Ltd.** declare that the reasons for this Class II permissive change are as below:

1. Software modification: upward compatibility of the Hardware changes
2. Support feature of the finger print clip;



After

before

The list of additional devices is mainly as follows:

R1440110023LA	MOS 管-P 沟道 MOS 管	P MOSFET	MOS-P, -12V, -10A, 0.012 Ω, DFN, 2.1*2.1*0.8	Prisemi	PPM6N12V10	1	Q1811
R1411400015LA	齐纳二极管	Zener Diode	Zener, 150mW, 3.3V, SOD523, 0.6	ROHM	EDZVFH3.3B	1	D1801
R1430110022LA	三极管-NPN 三极管	TRANSISTOR-BJT-NPN	TRANSISTOR-BJT-NPN, With Bias Resistor, VMT3	ROHM	DTC143TMT2L	1	Q1807
R1440120011LA	MOSFET (N 沟道)	DIODE	TRAN_N-channel with ESD protection, Vgs=+/-6V, SOT523	WILL	WNM4002-3/TR	1	Q1801

3. Support the anti-disassembly of front housing;

**Shanghai Sunmi Technology Co.,Ltd.**

Room 505, KIC Plaza, No.388 Song Hu Road, Yang Pu District, Shanghai, China  
Zhang Wentang 18721763396



After

before

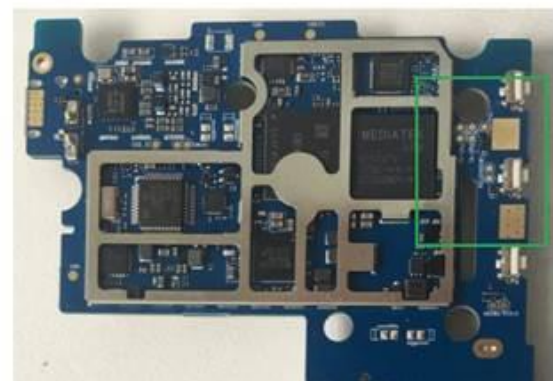
The list of additional devices is mainly as follows:

R6614000226LA	B0451_WALL_PCB_2层板_V1.0	PCB	B0451_WALL_PCB_2LAYER_V1.0_12.7*6.5 *1.5±0.1	深联	B0451_WALL_PCB_V1.0	1	W1401
---------------	-------------------------	-----	---	----	---------------------	---	-------

4. Support the anti-disassembly of front housing. Add another alarm position.



After



before

5. Add the VSYS feature (VSYS is VBAT)



Before



after

## Shanghai Sunmi Technology Co.,Ltd.

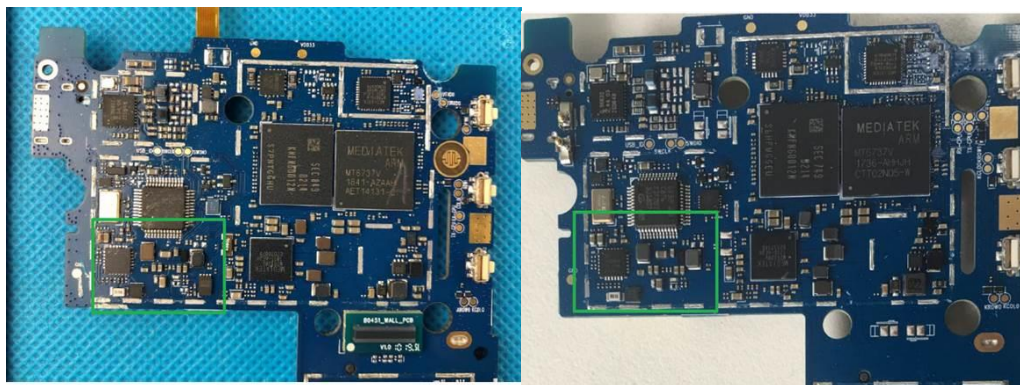
Room 505, KIC Plaza, No.388 Song Hu Road, Yang Pu District, Shanghai, China

Zhang Wentang 18721763396

The list of additional devices is mainly as follows:

R1150003324LA	单通道 LDO	IC-LDO	LDO, 3.3V/300MA, 1*1*0.37	WILL	WL2810D33-4/TR	1	U103
R1440120011LA	MOSFET(N 沟道)	DIODE	TRAN_N-channel with ESD protection, Vgs=+/-6V, SOT523	WILL	WNM4002-3/TR	1	Q103

### 6. Add Fuel Gauge



After

before

The list of additional devices is mainly as follows:

R1190011003LA	芯片-库仑计	IC-Fuel Gauge	IC-Fuel Gauge, I2C, 14bit ADC, TDFN8, 2*3*0.9	CellWise	CW2015CHBD	1	U0901
---------------	--------	---------------	---	----------	------------	---	-------

The list of change devices is mainly as follows:

Before the change							
R1110061015LA	8 路电平转换芯片	IC_LEVEL SHIFTER	IC_LEVEL SHIFTER, 8-bit, for push-pull, TQFN, 3.076*3.076*0.8	SGMICRO	SGM4568YTQG20G/TR	1	U1305
After the change							
R1150070053LA	8 路电平转换芯片	IC_LEVEL SHIFTER	IC_LEVEL SHIFTER, 8-bit, for push-pull, CSP20, 2.4*1.9*0.68	UNION	UM3308	1	U1301

7. change USB connector, USB change it from 14pin to 16pin

8. add an adapter TPA-23A050200UU01

Same as the original model except for the changes listed

Test assessment:

**Part15B:**

Re-test

**SAR:**

Worst case for each frequency

**RSE/EIRP/ERP:**

Worst case for 2/3/4G

**Shanghai Sunmi Technology Co.,Ltd.**

Room 505, KIC Plaza, No.388 Song Hu Road, Yang Pu District, Shanghai, China

Zhang Wentang 18721763396

---

**Thank you.**

**Sincerely,**

*Zhang Wentang*

---

**Zhang Wentang**

**Tel: +86- 18721763396**

**Email: zhangwentang@sunmi.com**